UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 7,084,030 B2 Page 1 of 1

APPLICATION NO.: 10/632496

DATED: August 1, 2006

INVENTOR(S): Chang-Hun Lee et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 4, line 3, the word "substrate" should read -- substrate, --;

Column 5, line 14, the words "order This" should read -- order. This --;

Column 14, line 39, the word "region," should read -- region; --;

Column 15, line 47, the word "high-conductivitiv" should read -- high-conductivity --;

Column 15, line 57, the word "fonning" should read -- forming --;

Column 15, line 59, the word "cefl" should read -- cell --;

Column 16, line 20, the word "flurther" should read -- further --;

Column 18, line 11, the word "high-conductivitiv" should read -- high-conductivity --;

Column 18, line 13, the word "sate" should read -- gate --;

Column 18, line 25, the word "gale" should read -- gate --.

Signed and Sealed this

Eighteenth Day of August, 2009

Varid J. Kappos

David J. Kappos

Director of the United States Patent and Trademark Office